

## **Process for forming a dual damascene structure**

### **ABSTRACT**

5       The invention describes a method for forming a dual  
damascene structure. An etch stop layer (150) is formed on  
a dielectric layer (140). A second dielectric layer (160)  
is formed on the etch stop layer (150) and an ARC layer  
(170) is formed the second dielectric layer. A first trench  
10 (185) and a second trench (195) are then simultaneously  
formed in the first and second dielectric layers (140) and  
(160) respectively.